

Silicon NPN Power Transistors

BU126

DESCRIPTION

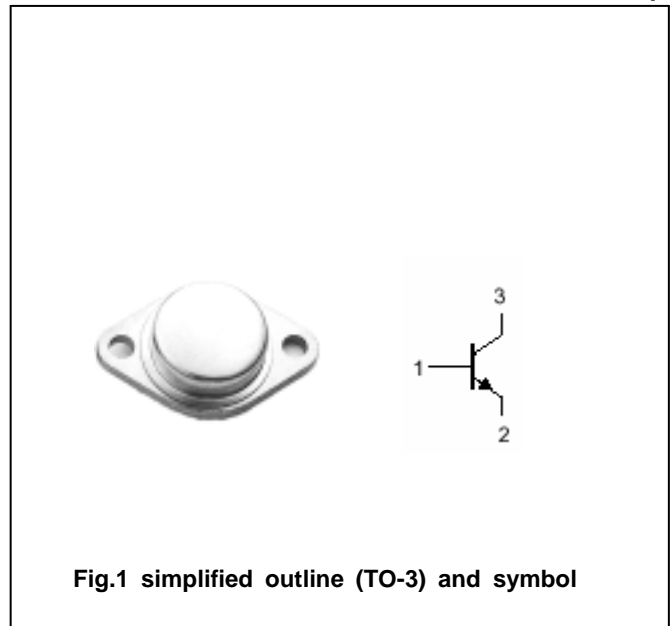
- With TO-3 package
- High breakdown voltage

APPLICATIONS

- For voltage regulator ,inverter,switching mode power supply applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	750	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
I_C	Collector current		3.0	A
I_{CM}	Collector current-peak		6.0	A
I_B	Base current		2.0	A
P_T	Total power dissipation	$T_C=25$	40	W
T_j	Junction temperature		125	
T_{stg}	Storage temperature		-65~125	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	2.5	K/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =0.1A; I _B =0;	300			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	6			V
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =2.5 A; I _B =0.25A			10	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =4 A; I _B =1A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4A; I _B =1A			1.5	V
I _{CES}	Collector cut-off current	V _{CE} =750V; V _{BE} =0 T _a =125			0.5 2	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =1A ; V _{CE} =5V	15			
C _{OB}	Output capacitance	I _E =0; V _{CB} =10V; f=0.5MHz		75		pF
f _T	Transition frequency	I _C =0.2 A ; V _{CE} =10V		10		MHz
t _f	Fall time	I _C =2.5A ; I _B =0.25A		0.2		μs

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PACKAGE OUTLINE

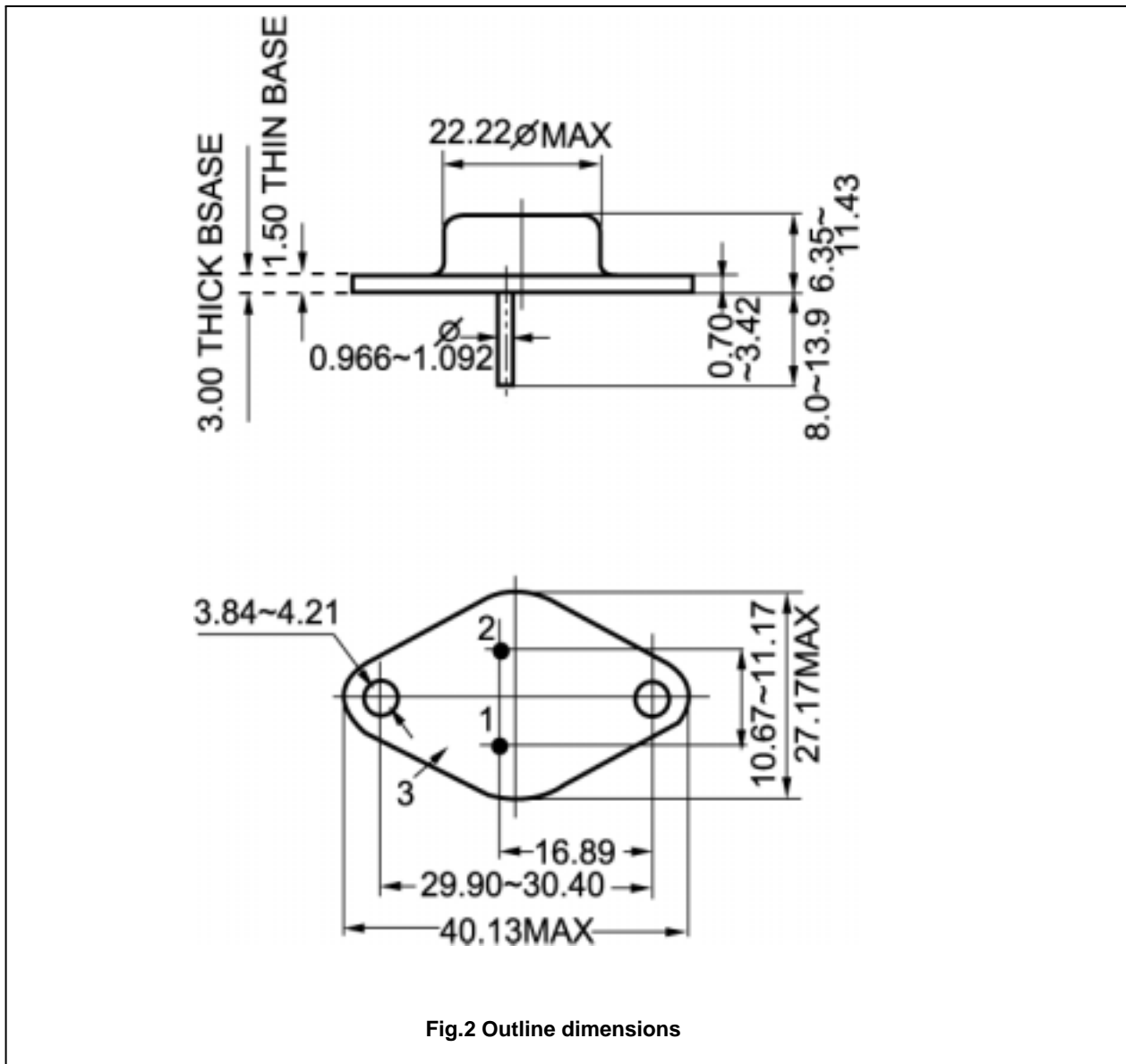


Fig.2 Outline dimensions